

IN THE CLAIMS:

Please cancel Claims 1, 2, and 5-8, without prejudice or disclaimer of subject matter. The following is a complete listing of claims and replaces all prior versions and listings of claims in the present application:

Claims 1-8 (cancelled).

Claim 9 (previously presented): A photoelectric conversion device comprising:

a plurality of pixels arranged in a pixel region, each pixel including a photoelectric conversion region for converting light into a signal charge, and a transfer transistor for transferring the signal charge from the photoelectric conversion region; and

a peripheral circuit arranged outside of the pixel region and including a circuit for processing the signal charge,

wherein the pixel region includes:

a first semiconductor region serving as a well of a first conductivity type disposed in the substrate of a second conductivity type that is opposite to the first conductivity type,

a second semiconductor region of the second conductivity type disposed in the first semiconductor region, being a part of the photoelectric conversion region and accumulating the signal charge, and

source and drain regions of the transfer transistor disposed in the first semiconductor region,

wherein the peripheral circuit includes:

a third semiconductor region serving as a well of the first conductivity type disposed in the substrate, and

source and drain regions of a transistor forming the peripheral circuit,

wherein an impurity concentration of the first semiconductor region is higher than an impurity concentration of the third semiconductor region, and

wherein the first semiconductor region extends deeper into the substrate than the third semiconductor region.